

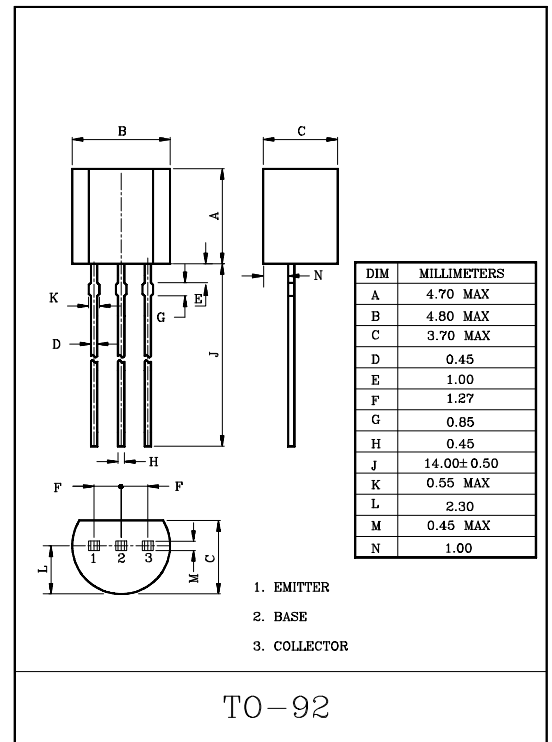
HIGH CURRENT APPLICATION.

FEATURE

- Complementary to MPS8050.

MAXIMUM RATINGS (Ta=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	-40	V
Collector-Emitter Voltage	V_{CEO}	-25	V
Emitter-Base Voltage	V_{EBO}	-6	V
Collector Current	I_C	-1.5	A
Collector Power Dissipation	P_C	625	mW
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{slg}	-55~150	°C



ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB} = -35V, I_E = 0$	-	-	-100	nA
Emitter Cut-off Current	I_{EBO}	$V_{EB} = -6V, I_C = 0$	-	-	-100	nA
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C = -100\mu A, I_E = 0$	-40	-	-	V
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = -2mA, I_B = 0$	-25	-	-	V
DC Current Gain	$h_{FE}(1)$	$V_{CE} = -1V, I_C = -5mA$	45	170	-	
	$h_{FE}(2)$ (Note)	$V_{CE} = -1V, I_C = -100mA$	85	160	300	
	$h_{FE}(3)$	$V_{CE} = -1V, I_C = -800mA$	40	80	-	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = -800mA, I_B = -80mA$	-	-0.28	-0.5	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = -800mA, I_B = -80mA$	-	-0.98	-1.2	V
Base-Emitter Voltage	V_{BE}	$V_{CE} = -1V, I_C = -10mA$	-	-0.66	-1.0	V
Transition Frequency	f_T	$V_{CE} = -10V, I_C = -50mA$	100	200	-	MHz
Collector Output Capacitance	C_{ob}	$V_{CB} = -10V, f = 1MHz, I_E = 0$	-	15	-	pF

Note : $h_{FE}(2)$ Classification B:85~160 , C : 120~200 , D : 160~300

